

MOSFETs Silicon N-Channel MOS ( $\pi$ -MOSVII)

# TK25A20D

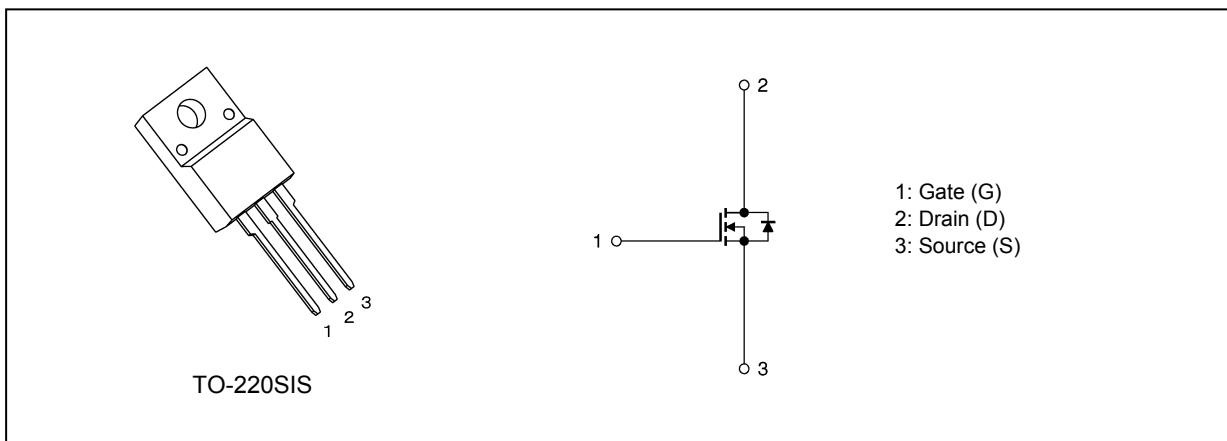
## 1. Applications

- Switching Voltage Regulators

## 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.047 \Omega$  (typ.)
- (2) Low leakage current:  $I_{DSS} = 10 \mu\text{A}$  (max) ( $V_{DS} = 200 \text{ V}$ )
- (3) Enhancement mode:  $V_{th} = 1.5$  to  $3.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	200	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	
Drain current (DC)	$I_D$	25	A
Drain current (pulsed)	$I_{DP}$	100	
Power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	45	W
Single-pulse avalanche energy	$E_{AS}$	118	mJ
Avalanche current	$I_{AR}$	25	A
Reverse drain current (DC)	$I_{DR}$	25	
Reverse drain current (pulsed)	$I_{DRP}$	100	
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to 150	
Isolation voltage (RMS) ( $t = 1.0 \text{ s}$ )	$V_{ISO(\text{RMS})}$	2000	V
Mounting torque	$T_{OR}$	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Start of commercial production  
2011-02

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	2.78	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	62.5	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 50$  V,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.3$  mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 25$  A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

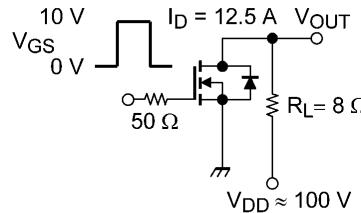
## 6. Electrical Characteristics

### 6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$	—	—	$\pm 1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}$ , $V_{GS} = 0\text{ V}$	200	—	—	V
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}$ , $I_D = 1\text{ mA}$	1.5	—	3.5	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}$ , $I_D = 12.5\text{ A}$	—	0.047	0.07	$\Omega$

### 6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	—	2550	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	21	—	
Output capacitance	$C_{oss}$		—	180	—	
Gate resistance	$r_g$	$V_{DS} = \text{OPEN}$ , $f = 1\text{ MHz}$	—	6.3	—	$\Omega$
Switching time (rise time)	$t_r$	See Figure 6.2.1.	—	73	—	ns
Switching time (turn-on time)	$t_{on}$		—	120	—	
Switching time (fall time)	$t_f$		—	66	—	
Switching time (turn-off time)	$t_{off}$		—	360	—	



Duty  $\leq 1\%$ ,  $t_w = 10\text{ }\mu\text{s}$

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 160\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 25\text{ A}$	—	60	—	$\text{nC}$
Gate-source charge 1	$Q_{gs1}$		—	11	—	
Gate-drain charge	$Q_{gd}$		—	22	—	

### 6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	$V_{DSF}$	$I_{DR} = 25\text{ A}$ , $V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 25\text{ A}$ , $V_{GS} = 0\text{ V}$	—	195	—	ns
Reverse recovery charge	$Q_{rr}$	$-dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	1.6	—	$\mu\text{C}$
Peak reverse recovery current	$I_{rr}$		—	16	—	A

## 7. Marking (Note)

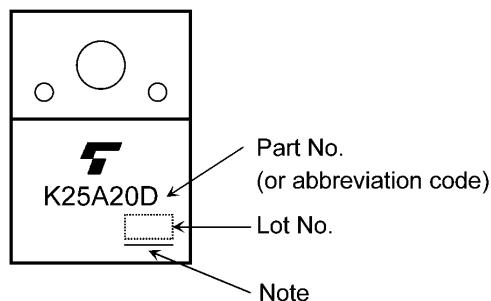


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

## 8. Characteristics Curves (Note)

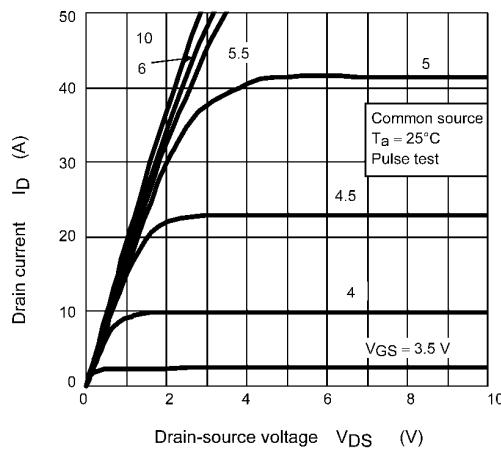


Fig. 8.1  $I_D$  -  $V_{DS}$

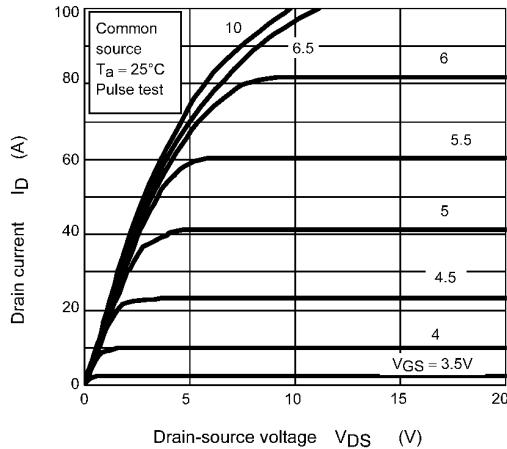


Fig. 8.2  $I_D$  -  $V_{DS}$

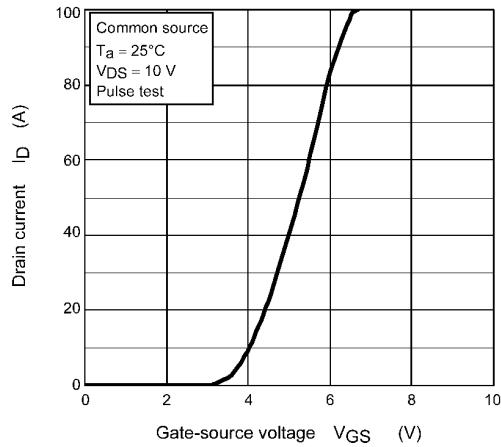


Fig. 8.3  $I_D$  -  $V_{GS}$

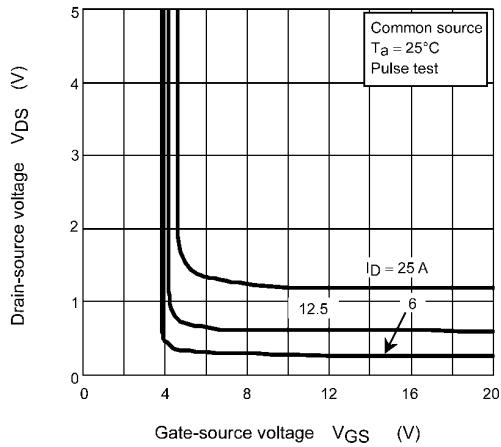


Fig. 8.4  $V_{DS}$  -  $V_{GS}$

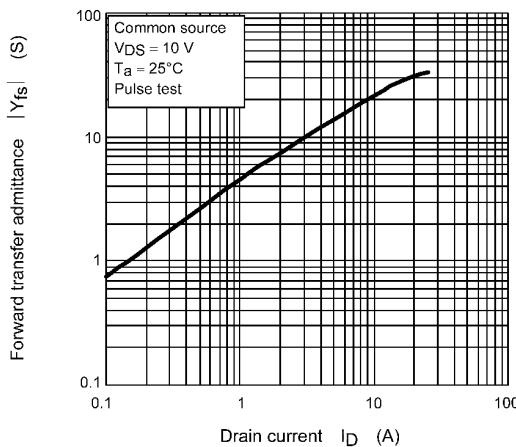


Fig. 8.5  $|Y_{fs}|$  -  $I_D$

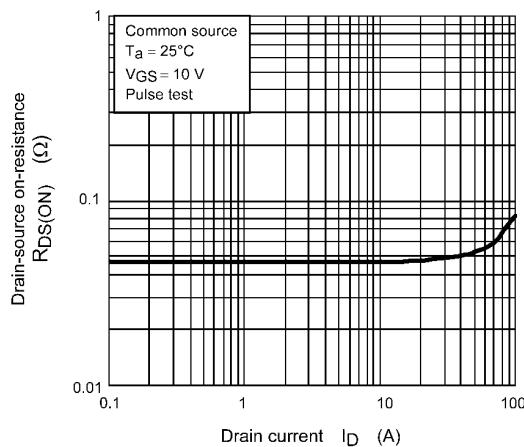


Fig. 8.6  $R_{DS(\text{ON})}$  -  $I_D$

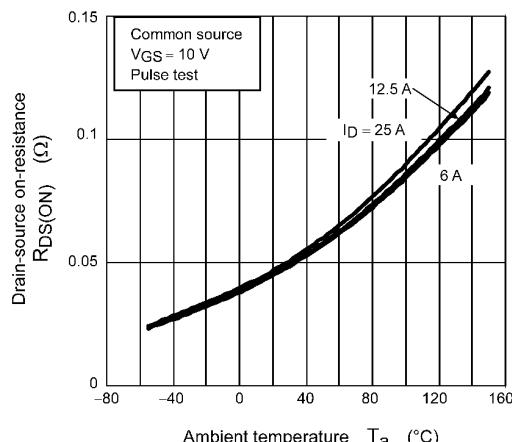
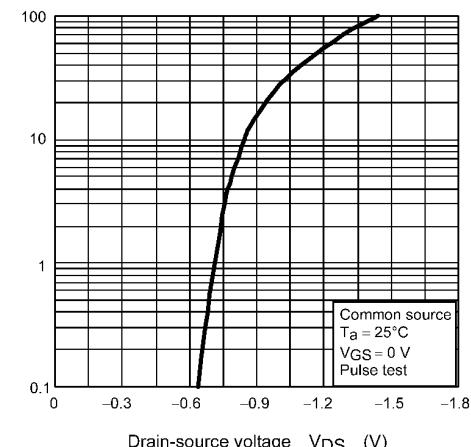
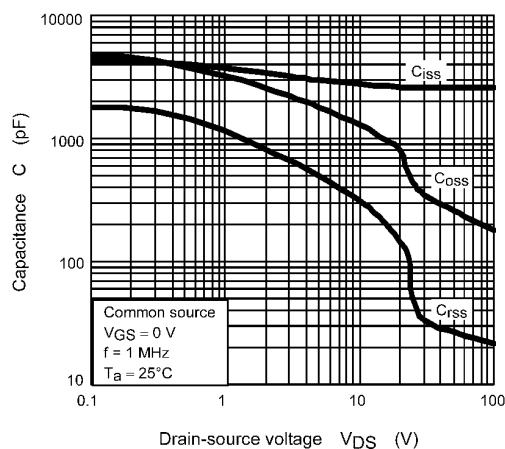
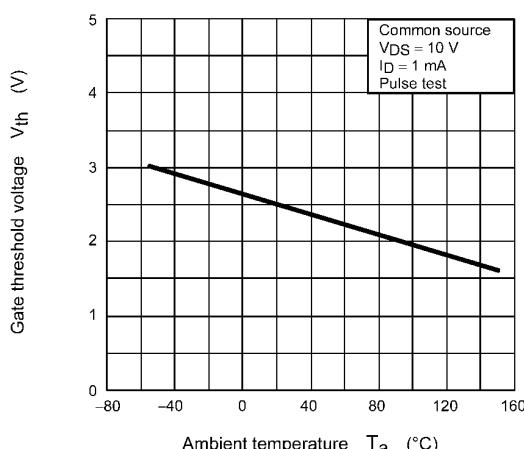
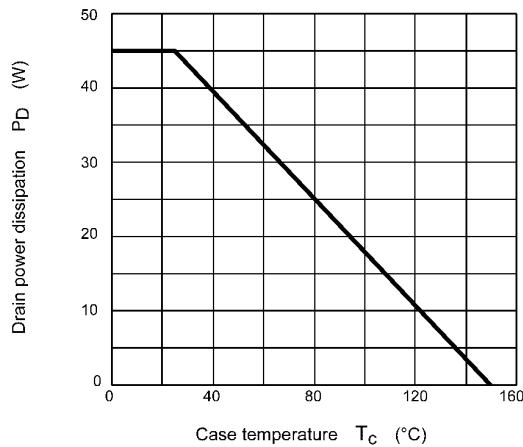
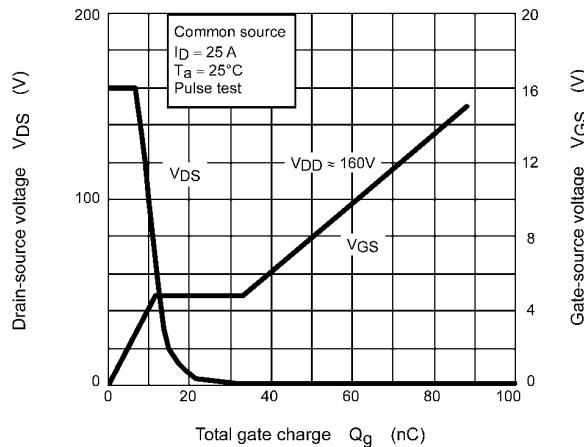
Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>Fig. 8.9 C - V<sub>DS</sub>Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>Fig. 8.11 P<sub>D</sub> - T<sub>c</sub>  
(Guaranteed Maximum)

Fig. 8.12 Dynamic Input/Output Characteristics

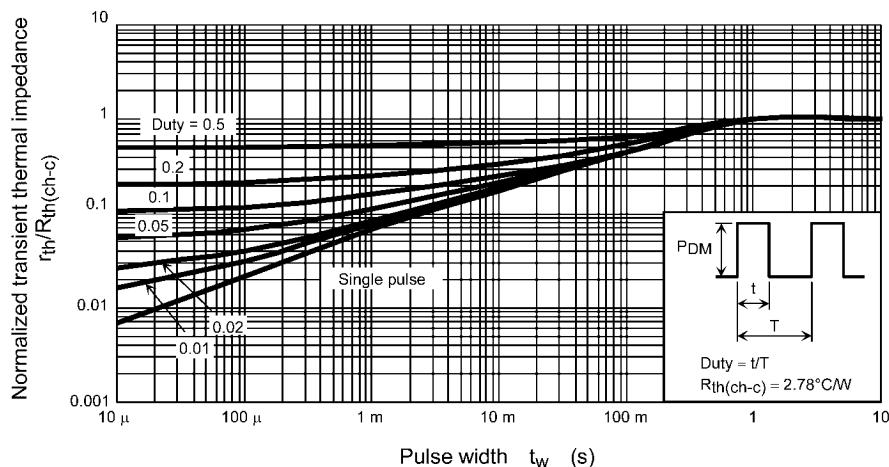


Fig. 8.13  $r_{th}/R_{th(ch-c)}$  -  $t_w$   
(Guaranteed Maximum)

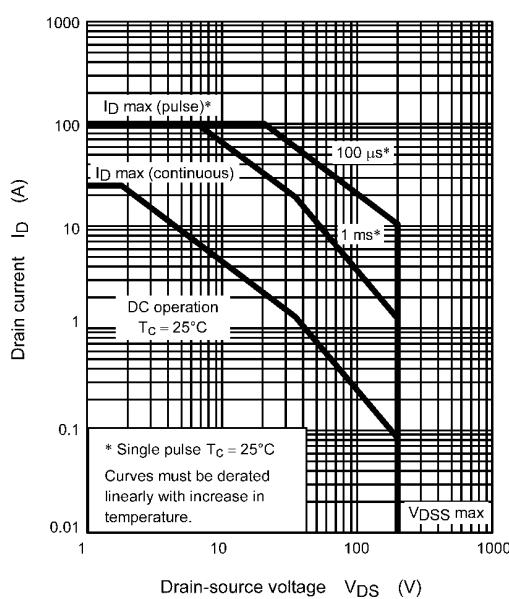


Fig. 8.14 Safe Operating Area  
(Guaranteed Maximum)

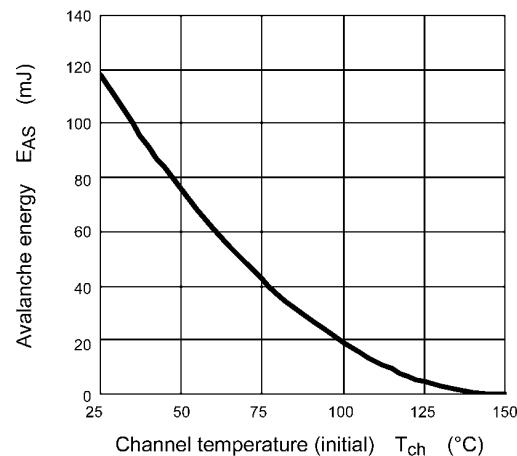
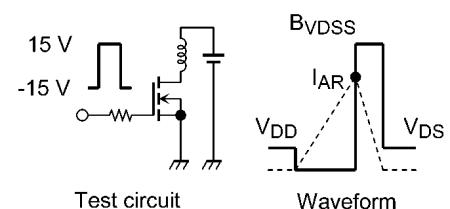


Fig. 8.15  $E_{AS}$  -  $T_{ch}$   
(Guaranteed Maximum)



$$R_G = 25 \Omega$$

$$V_{DD} = 50 \text{ V}, L = 0.3 \text{ mH}$$

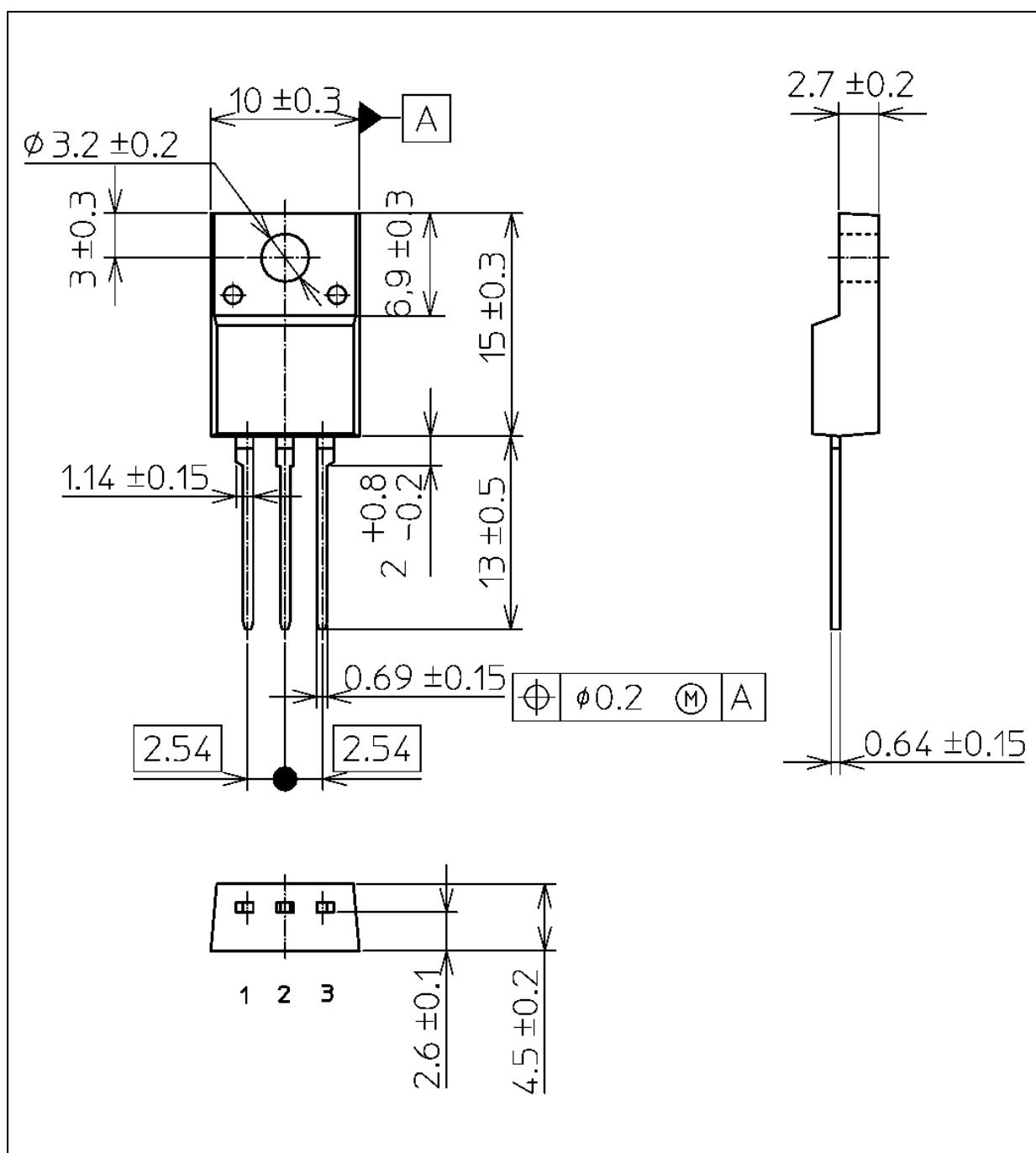
$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

Package Name(s)
JEITA: SC-67
TOSHIBA: 2-10U1S
Nickname: TO-220SIS

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